

6MBI50UA-120



IGBT Module U-Series 1200V / 50A 6 in one-package

■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item		Symbol	Conditions		Rating	Unit
Collector-Emitter voltage		V _{CES}			1200	V
Gate-Emitter voltage		V _{GES}			±20	V
Collector current		I _c	Continuous	T _c =25°C	75	A
				T _c =80°C	50	
		I _{cp}	1ms	T _c =25°C	150	
				T _c =80°C	100	
		-I _c			50	
		-I _c pulse			100	
Collector Power Dissipation		P _c	1 device		275	W
Junction temperature		T _j			+150	°C
Storage temperature		T _{slg}			-40 to +125	
Isolation voltage	between terminal and copper base *1	V _{iso}	AC:1min.		2500	VAC
	between thermistor and others *2					
Screw Torque	Mounting *3	-			3.5	N·m

*1 : All terminals should be connected together when isolation test will be done.

*2 : Two thermistor terminals should be connected together, each other terminals should be connected together and shorted to base plate when isolation test will be done.

*3 : Recommendable value : 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at T_j=25°C unless otherwise specified)

Item		Symbols	Conditions		Characteristics			Unit
					Min.	Typ.	Max.	
Inverter	Zero gate voltage collector current	ICES	VGE=0V, VCE=1200V		—	—	1.0	mA
	Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V		—	—	200	nA
	Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=50mA		4.5	6.5	8.5	V
	Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V, IC=50A	TJ=25°C	—	2.00	2.35	V
				TJ=125°C	—	2.25	—	
		VCE(sat) (chip)		TJ=25°C	—	1.75	2.10	
				TJ=125°C	—	2.00	—	
	Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz		—	6	—	nF
	Turn-on time	ton	VCC=600V IC=50A VGE=±15V		—	0.36	1.20	μs
		tr			—	0.21	0.60	
		tr(i)			—	0.03	—	
	Turn-off time	toff	RG=22 Ω		—	0.37	1.00	
		tf			—	0.07	0.30	
	Forward on voltage	VF (terminal)	VGE=0V IF=50A	TJ=25°C	—	1.85	2.15	V
TJ=125°C				—	1.95	—		
VF (chip)		TJ=25°C		—	1.60	1.90		
		TJ=125°C		—	1.70	—		
Reverse recovery time	trr	IF=50A		—	—	0.35	μs	
Lead resistance, terminal-chip*4	R lead			—	4.1	—	mΩ	
Thermistor	Resistance	R	T=25°C		—	5000	—	Ω
		T=100°C		465	495	520		
	B value	B	T=25/50°C		3305	3375	3450	K

*4:Biggest internal terminal resistance among arm.

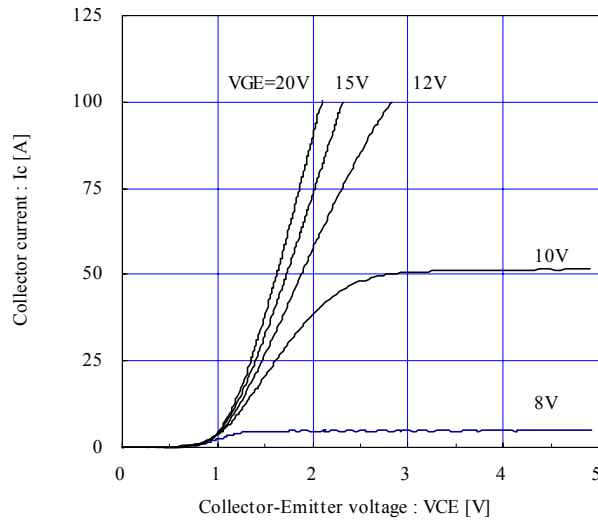
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	R _{th(j-c)}	IGBT	—	—	0.45	°C/W
	R _{th(j-c)}	FWD	—	—	0.73	°C/W
Contact Thermal resistance	R _{th(c-f)} *5	With thermal compound	—	0.05	—	°C/W

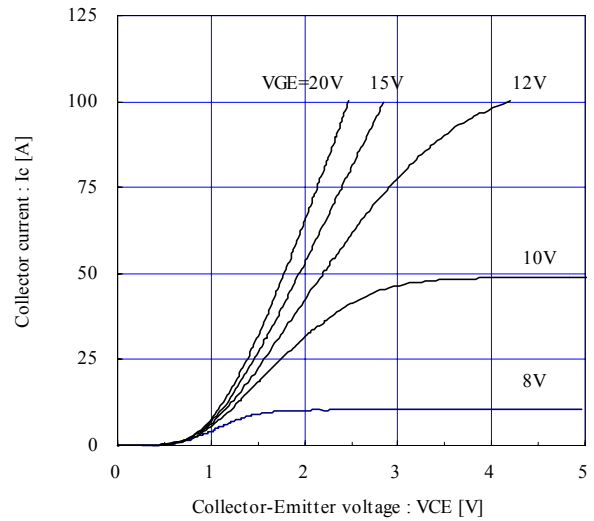
*5 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.)

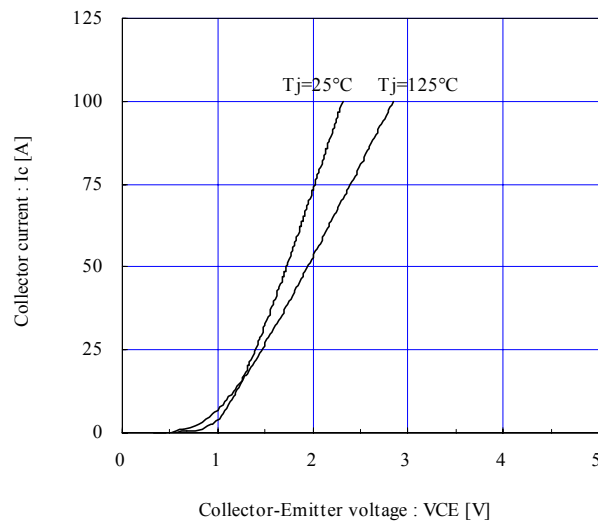
 $T_j = 25^\circ\text{C}$ / chip

Collector current vs. Collector-Emitter voltage (typ.)

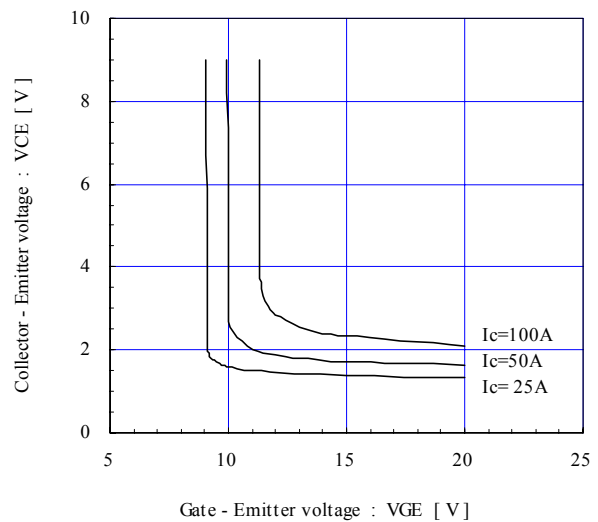
 $T_j = 125^\circ\text{C}$ / chip

Collector current vs. Collector-Emitter voltage (typ.)

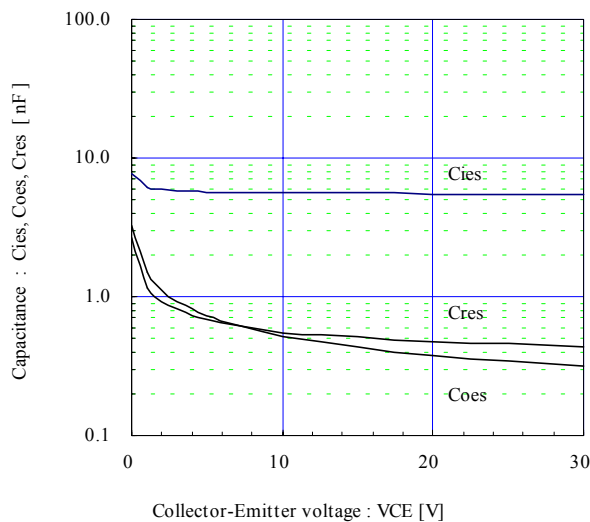
VGE = 15V / chip



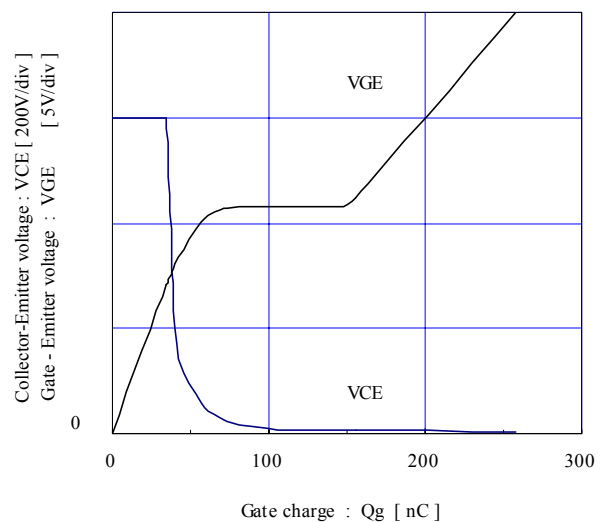
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

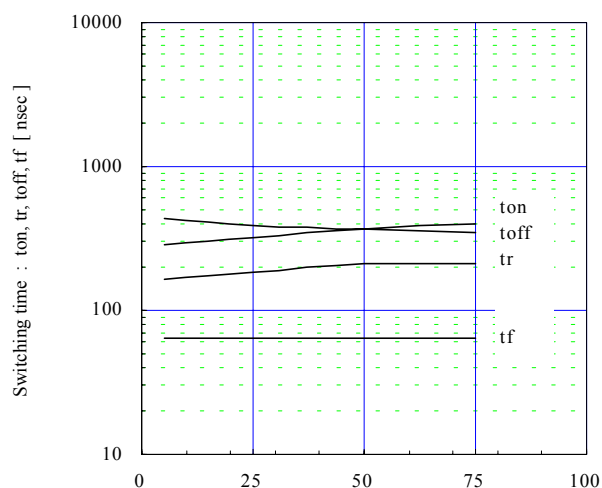
Capacitance vs. Collector-Emitter voltage (typ.)

VGE = 0V, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$ 

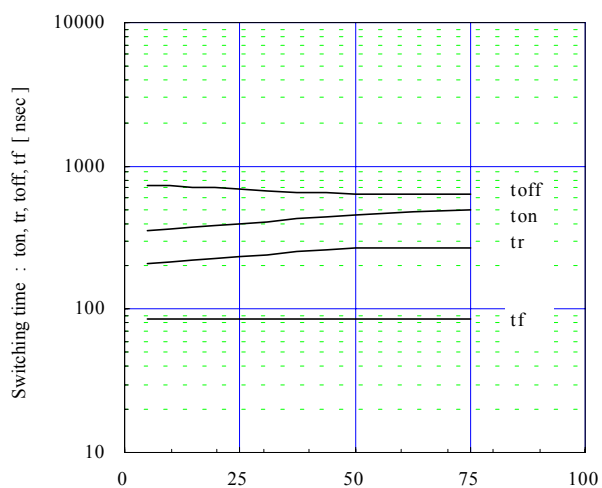
Dynamic Gate charge (typ.)

Vce = 600V, Ic = 50A, $T_j = 25^\circ\text{C}$ 

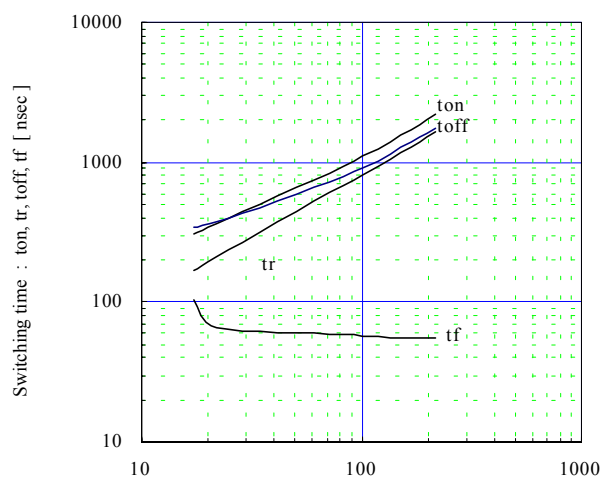
Switching time vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega, T_j=25^\circ C$ 

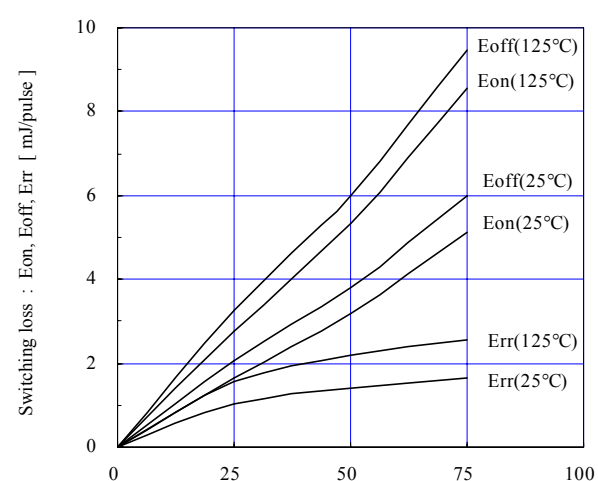
Switching time vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega, T_j=125^\circ C$ 

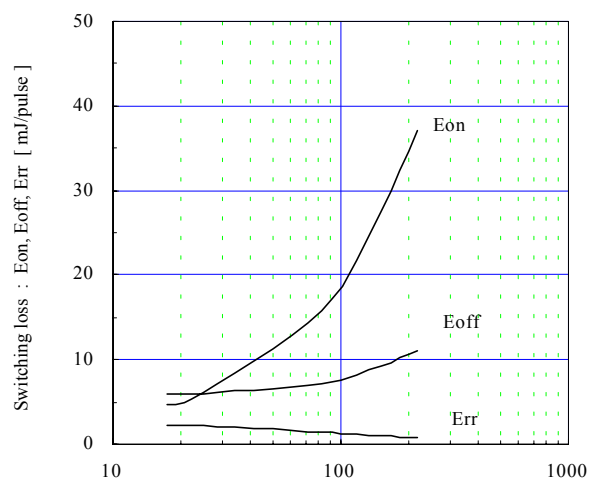
Switching time vs. Gate resistance (typ.)

 $V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V, T_j=25^\circ C$ 

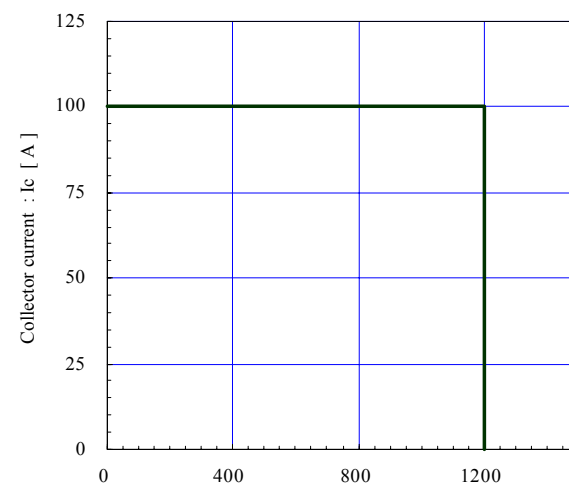
Switching loss vs. Collector current (typ.)

 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega$ 

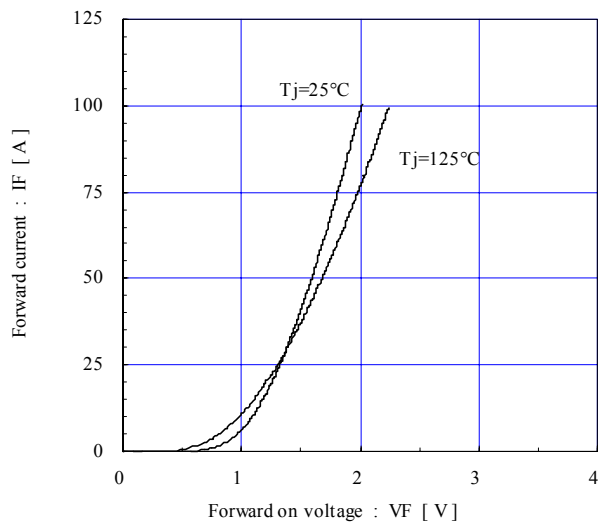
Switching loss vs. Gate resistance (typ.)

 $V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V, T_j=125^\circ C$ 

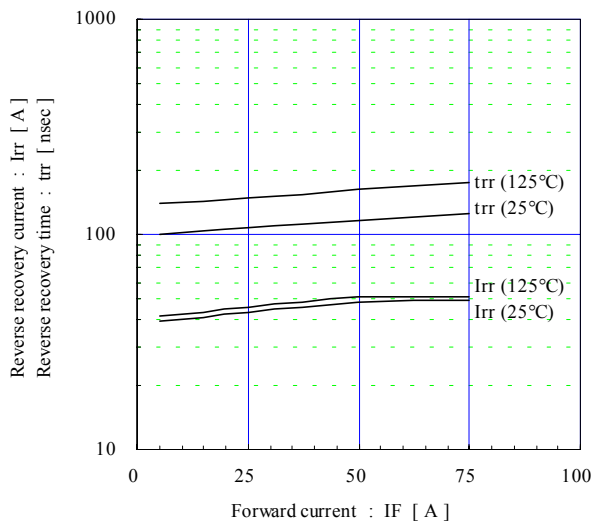
Reverse bias safe operating area (max.)

 $+V_{GE}=15V, -V_{GE} \leq 15V, R_g \geq 22\Omega, T_j \leq 125^\circ C$ 

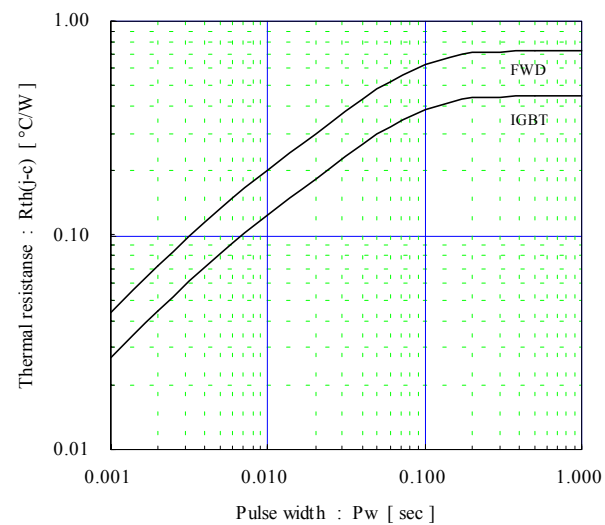
Forward current vs. Forward on voltage (typ.)
chip



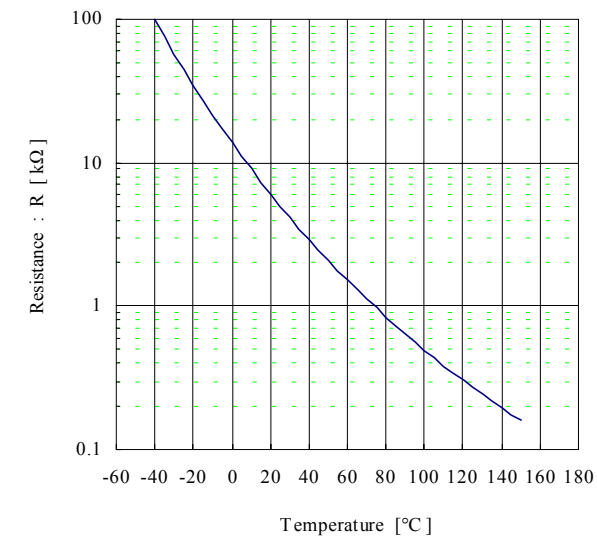
Reverse recovery characteristics (typ.)
Vcc=600V, VGE=±15V, Rg=22Ω



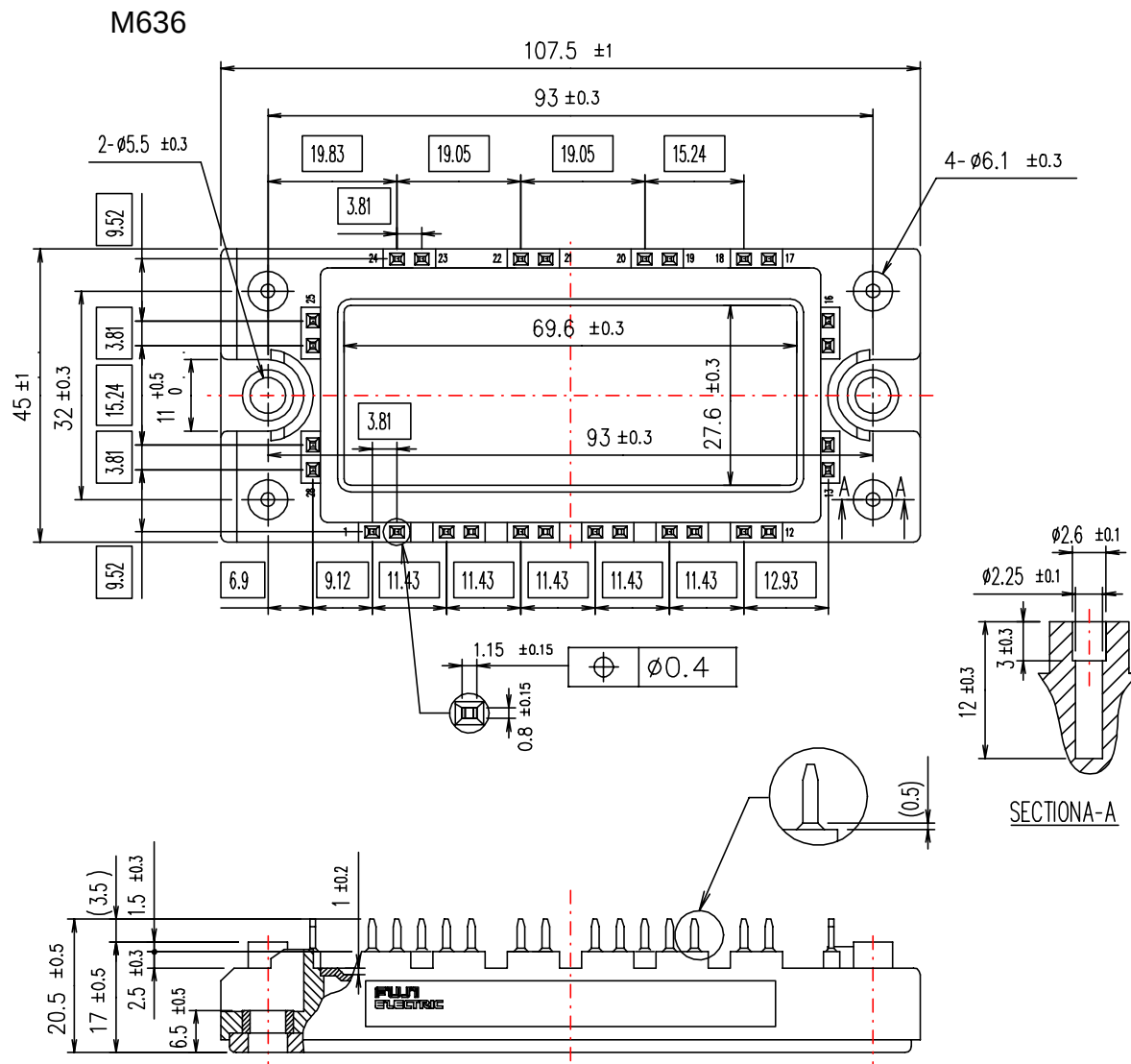
Transient thermal resistance (max.)



Temperature characteristic (typ.)



Outline Drawings, mm



□ shows theoretical dimension.

() shows reference dimension.

Equivalent Circuit Schematic

